



STP110N55F6

N-channel 55 V, 4.3 m Ω , 110 A TO-220
STripFET™ VI DeepGATE™ Power MOSFET

Preliminary data

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D
STP110N55F6	55 V	< 5.2 m Ω	110 A

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

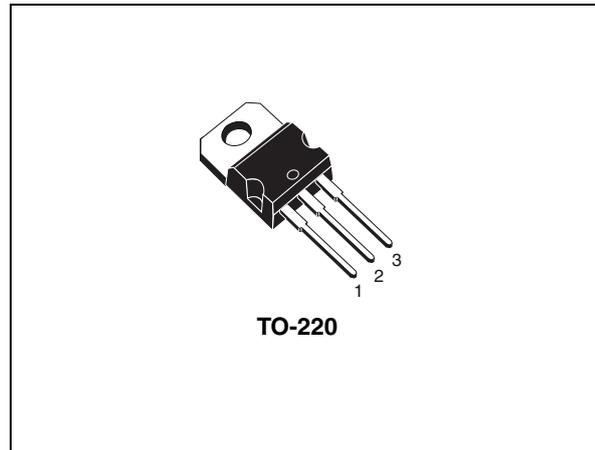


Figure 1. Internal schematic diagram

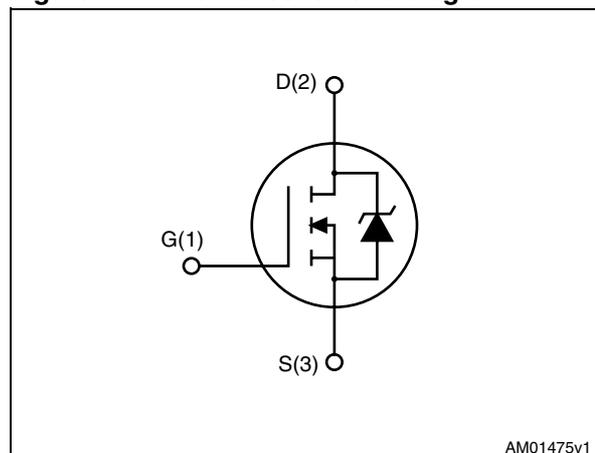


Table 1. Device summary

Order code	Marking	Package	Packaging
STP110N55F6	110N55F6	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	55	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	110	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	78.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	440	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
	Derating factor	1	W/ $^\circ\text{C}$
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\ \mu\text{A}$	55			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 60\text{ A}$		4.3	5.2	$\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			8350		pF
C_{oss}	Output capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	460	-	pF
C_{rss}	Reverse transfer capacitance			344		pF
Q_g	Total gate charge	$V_{DD} = 44\text{ V}, I_D = 110\text{ A},$ $V_{GS} = 10\text{ V}$ <i>(see Figure 3)</i>		120		nC
Q_{gs}	Gate-source charge		-	TBD	-	nC
Q_{gd}	Gate-drain charge			TBD		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 44\text{ V}, I_D = 55\text{ A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ <i>(see Figure 2)</i>	-	TBD	-	ns
t_r	Rise time		-	TBD	-	ns
$t_{d(off)}$	Turn-off-delay time	$V_{DD} = 44\text{ V}, I_D = 55\text{ A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ <i>(see Figure 2)</i>	-	TBD	-	ns
t_f	Fall time		-	TBD	-	ns

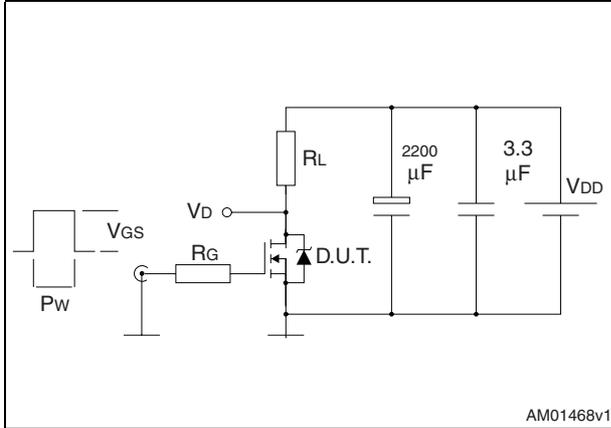
Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		110	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		440	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 110 \text{ A}, V_{GS} = 0$	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 110 \text{ A}, V_{DD} = 44 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$, $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 4)	-	TBD TBD TBD		ns nC A

1. Current limited by package.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

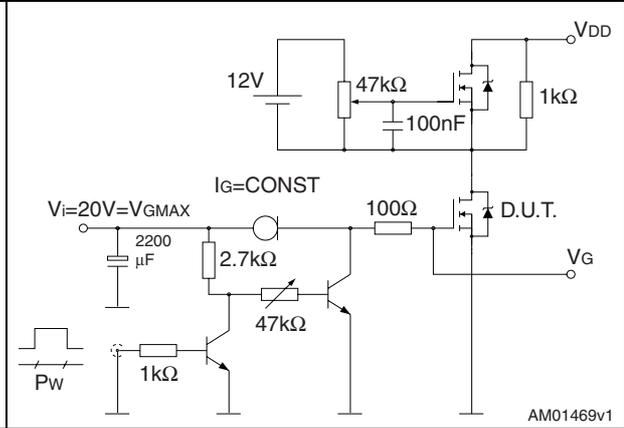
3 Test circuits

Figure 2. Switching times test circuit for resistive load



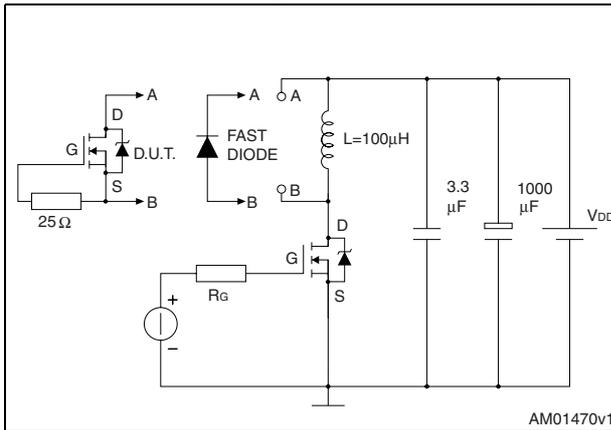
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Figure 3. Gate charge test circuit



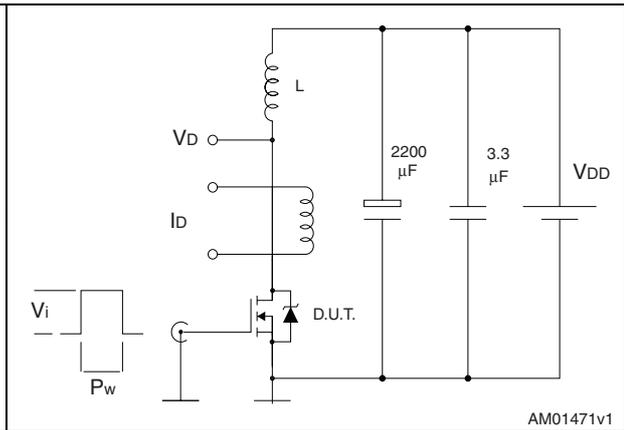
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Figure 4. Test circuit for inductive load switching and diode recovery times



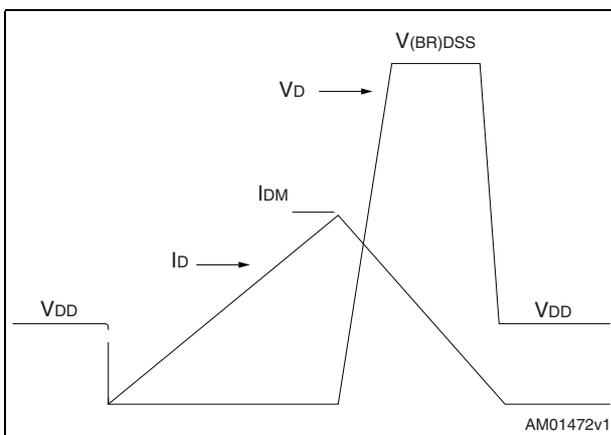
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Figure 5. Unclamped inductive load test circuit



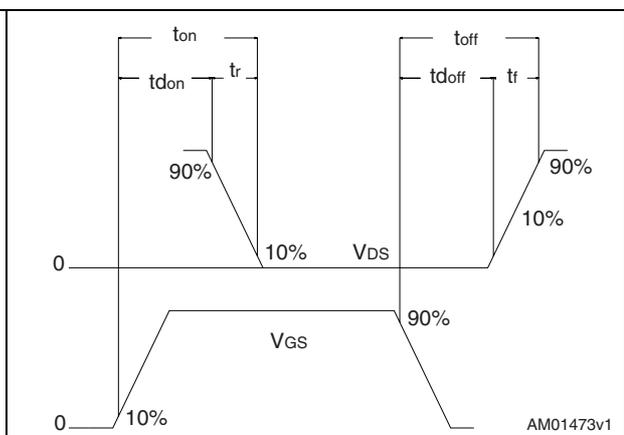
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Figure 6. Unclamped inductive waveform



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Figure 7. Switching time waveform



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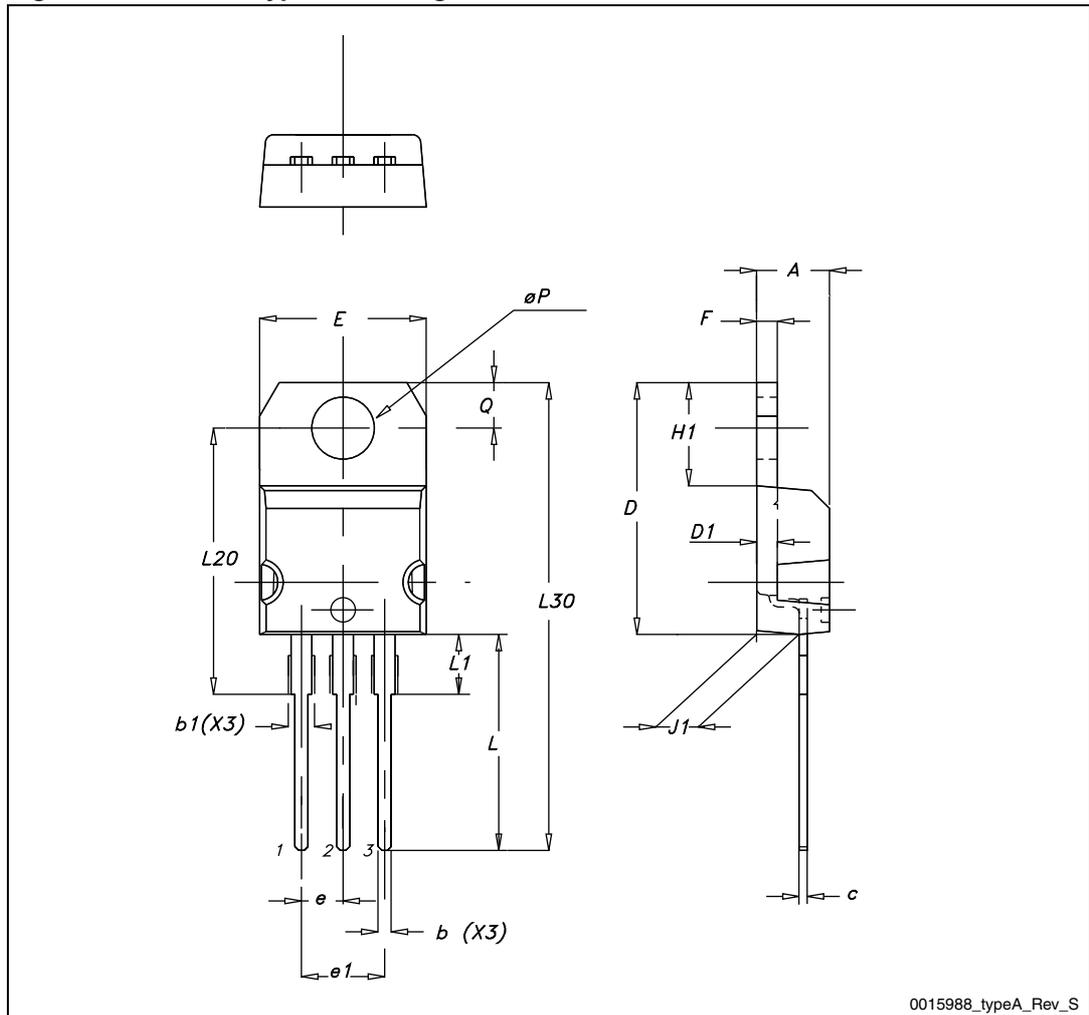
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 8. TO-220 type A drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
18-Jul-2011	1	First release.

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